NSN 5961-00-528-8682

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View Online at https://aerobasegroup.com/nsn/5961-00-528-8682 **Inclosure Material:** Metal **Overall Length:** 1.573 inches **Overall Height:** 0.225 inches **Overall Width:** 1.050 inches **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: **Component Name And Quantity:** 2 transistor **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 80.0 breakdown voltage, collector-to-base, emitter open all transistor and 80.0 breakdown voltage, collector-to-emitter, with specified resistance between base and emitter all transistor and 8.0 emitter to base voltage, static, collector open all transistor **Current Rating Per Characteristic:** 10.00 amperes source cutoff current all transistor **Power Rating Per Characteristic:** 50.0 watts small-signal input power, common-collector preset all transistor **Transfer Ratio:** 800.0 static forward current transfer ratio, common-emitter all transistor **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction **Special Features:** All transistor junction pattern arrangement: npn **Precious Material And Location:** Lead surfaces gold **Precious Material:** Gold **Terminal Type And Quantity:** 8 pin

N/a

Shelf Life:

Unit Of Measure:

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Demilitarization:

No

Fiig:

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